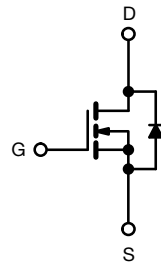
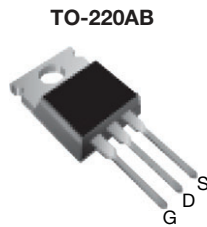


Power MOSFET



N-Channel MOSFET

FEATURES

- Dynamic dV/dt rating
- 175 °C operating temperature
- Fast switching
- Ease of paralleling
- Simple drive requirements
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS*
Available

Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

DESCRIPTION

Third generation power MOSFETs from Vishay provides the designer with the best combination of fast switching, ruggedized device design, low on-resistance, and cost effectiveness.

The TO-220AB package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 W. The low thermal resistance and low package cost of the TO-220AB contribute to its wide acceptance throughout the industry.

PRODUCT SUMMARY

V_{DS} (V)	60	
$R_{DS(on)}$ (Ω)	$V_{GS} = 10$ V	0.20
Q_g (Max.) (nC)	11	
Q_{gs} (nC)	3.1	
Q_{gd} (nC)	5.8	
Configuration	Single	

ORDERING INFORMATION

Package	TO-220AB
Lead (Pb)-free	IRFZ10PbF

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	V_{DS}	60	V	
Gate-source voltage	V_{GS}	± 20		
Continuous drain current	V_{GS} at 10 V	$T_C = 25$ °C	10	A
		$T_C = 100$ °C	7.2	
Pulsed drain current ^a	I_{DM}	40		
Linear derating factor		0.29	W/°C	
Single pulse avalanche energy ^b	E_{AS}	47	mJ	
Maximum power dissipation	$T_C = 25$ °C	P_D	43	W
Peak diode recovery dV/dt ^c	dV/dt	4.5	V/ns	
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +175	°C	
Soldering recommendations (peak temperature)	For 10 s	300 ^d		
Mounting torque	6-32 or M3 screw	10		lbf · in
		1.1	N · m	

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- $V_{DD} = 25$ V, starting $T_J = 25$ °C, $L = 1.8$ mH, $R_g = 25$ Ω , $I_{AS} = 7.2$ A (see fig. 12)
- $I_{SD} \leq 10$ A, $dI/dt \leq 90$ A/ μ s, $V_{DD} \leq V_{DS}$, $T_J \leq 175$ °C
- 1.6 mm from case

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R_{thJA}	-	62	°C/W
Case-to-sink, flat, greased surface	R_{thCS}	0.50	-	
Maximum junction-to-case (drain)	R_{thJC}	-	3.5	

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		60	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$		-	0.063	-	V/°C
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2.0	-	4.0	V
Gate-source leakage	I_{GSS}	$V_{GS} = \pm 20$		-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$		-	-	25	μA
		$V_{DS} = 48\text{ V}, V_{GS} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$		-	-	250	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 6.0\text{ A}^b$	-	-	0.20	Ω
Forward transconductance	g_{fs}	$V_{DS} = 25\text{ V}, I_D = 6.0\text{ A}^b$		2.4	-	-	S
Dynamic							
Input capacitance	C_{iss}	$V_{GS} = 0\text{ V}$ $V_{DS} = 25\text{ V}$ $f = 1.0\text{ MHz}$, see fig. 5		-	300	-	pF
Output capacitance	C_{oss}			-	160	-	
Reverse transfer capacitance	C_{rss}			-	29	-	
Total gate charge	Q_g	$V_{GS} = 10\text{ V}$	$I_D = 10\text{ A}, V_{DS} = 48\text{ V}$, see fig. 6 and 13 ^b	-	-	11	nC
Gate-source charge	Q_{gs}			-	-	3.1	
Gate-drain charge	Q_{gd}			-	-	5.8	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 30\text{ V}, I_D = 10\text{ A}$ $R_g = 24\text{ }\Omega, R_D = 2.7\text{ }\Omega$, see fig. 10 ^b		-	10	-	ns
Rise time	t_r			-	50	-	
Turn-off delay time	$t_{d(off)}$			-	13	-	
Fall time	t_f			-	19	-	
Internal drain inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact		-	4.5	-	nH
Internal source inductance	L_S			-	7.5	-	
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I_S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	10	A
Pulsed diode forward current ^a	I_{SM}			-	-	40	
Body diode voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = 10\text{ A}, V_{GS} = 0\text{ V}^b$		-	-	1.6	V
Body diode reverse recovery time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = 10\text{ A}, di/dt = 100\text{ A}/\mu\text{s}^b$		-	70	140	ns
Body diode reverse recovery charge	Q_{rr}			-	0.20	0.40	μC
Forward turn-on time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
 b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

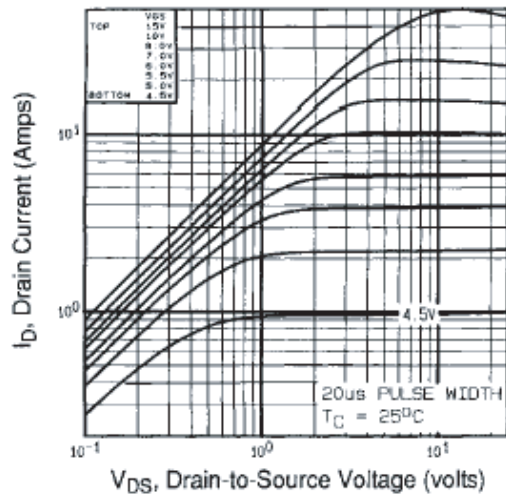


Fig. 1 - Typical Output Characteristics, $T_C = 25\text{ }^\circ\text{C}$

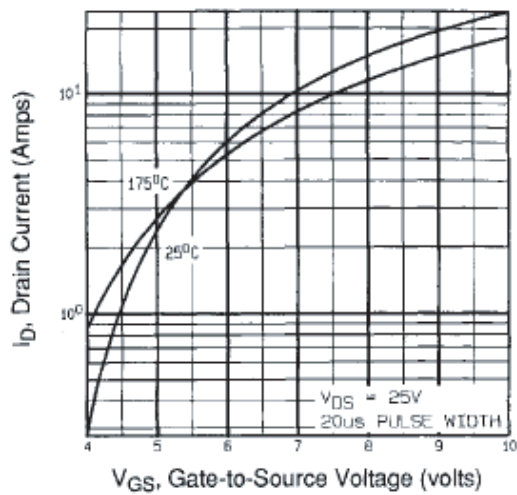


Fig. 3 - Typical Transfer Characteristics

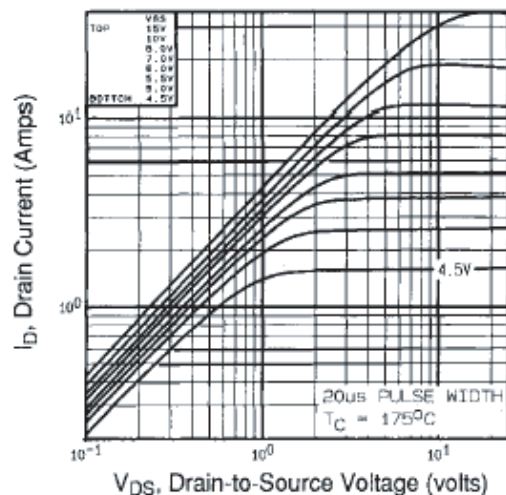


Fig. 2 - Typical Output Characteristics, $T_C = 175\text{ }^\circ\text{C}$

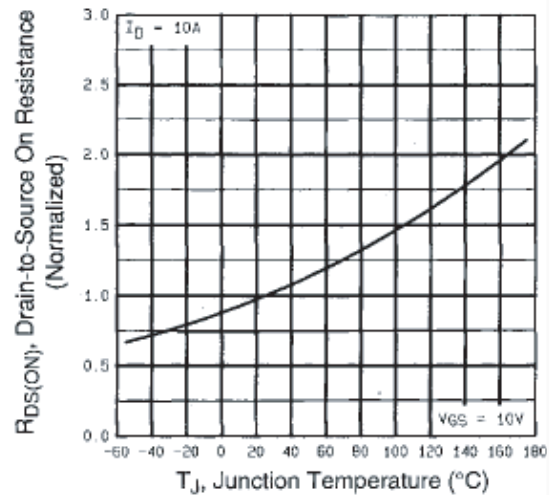


Fig. 4 - Normalized On-Resistance vs. Temperature

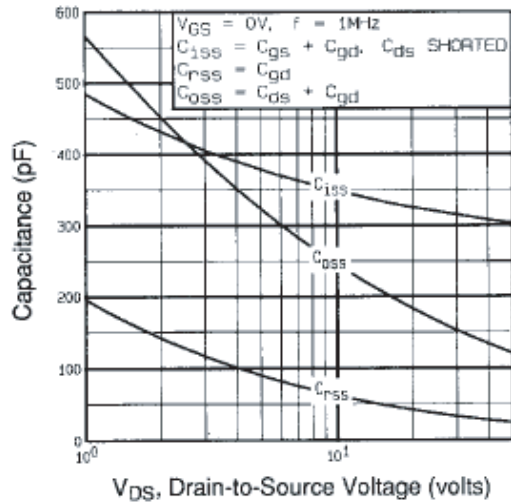


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

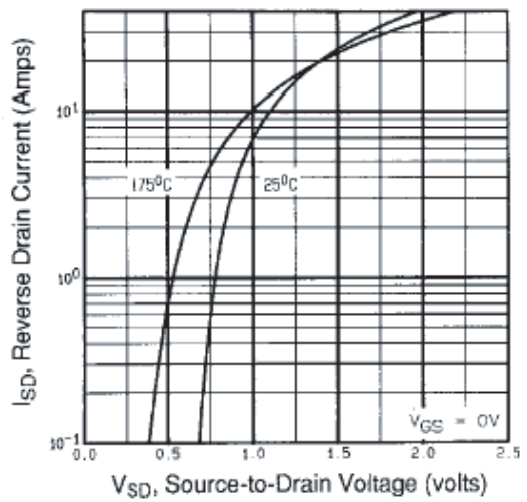


Fig. 7 - Typical Source-Drain Diode Forward Voltage

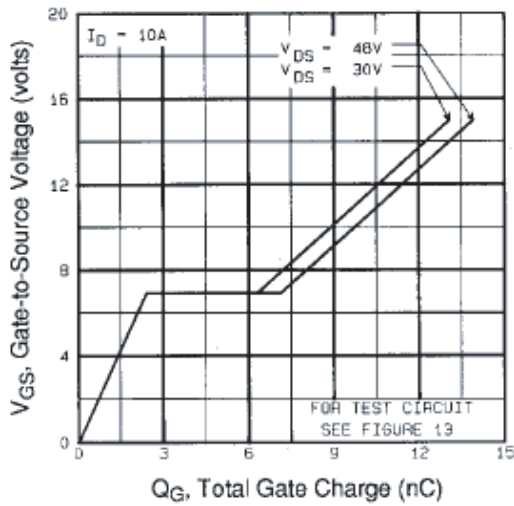


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

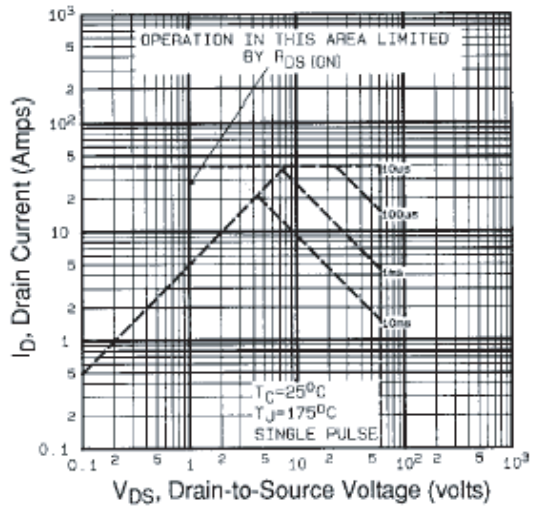


Fig. 8 - Maximum Safe Operating Area

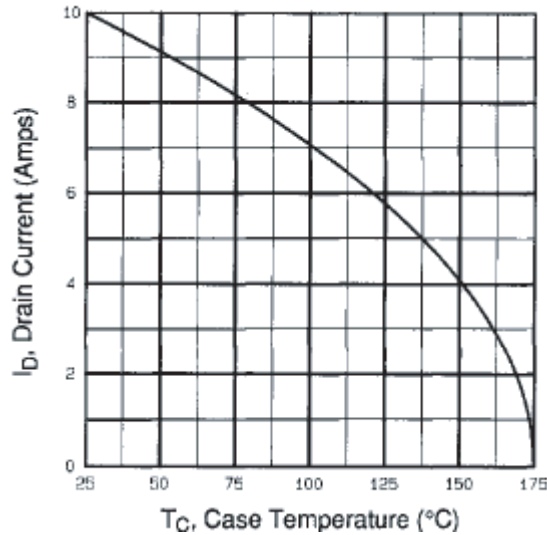


Fig. 9 - Maximum Drain Current vs. Case Temperature

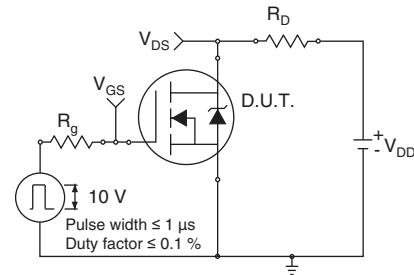


Fig. 10a - Switching Time Test Circuit

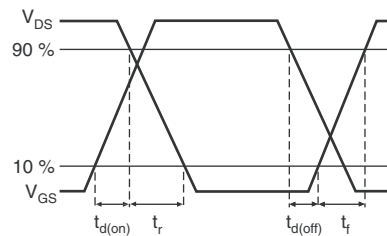


Fig. 10b - Switching Time Waveforms

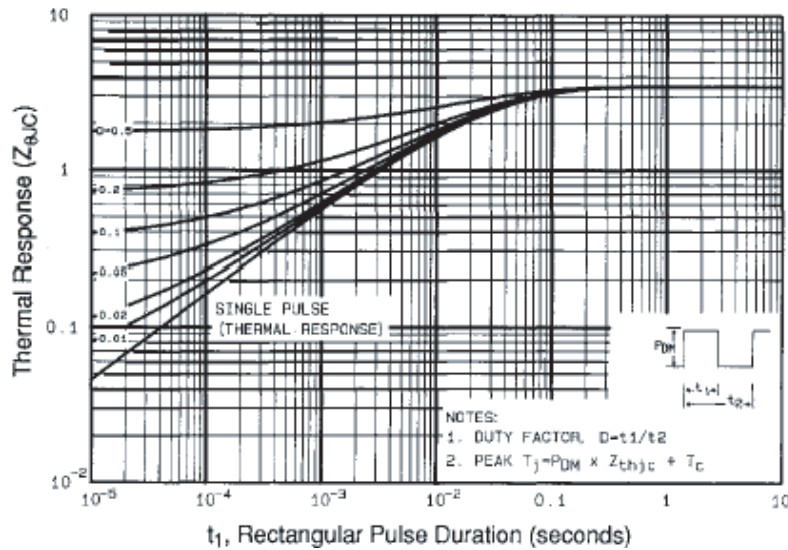


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

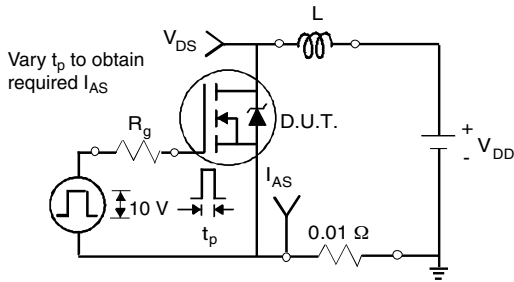


Fig. 12a - Unclamped Inductive Test Circuit

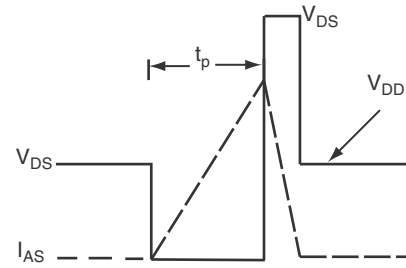


Fig. 12b - Unclamped Inductive Waveforms

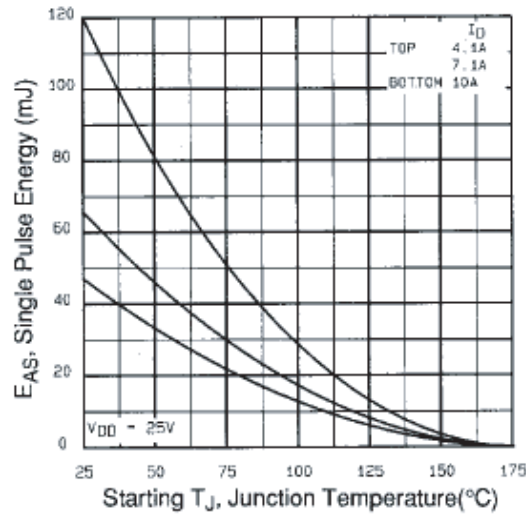


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

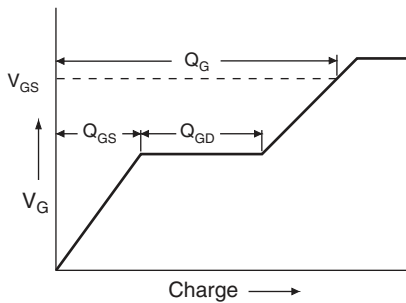


Fig. 13a - Basic Gate Charge Waveform

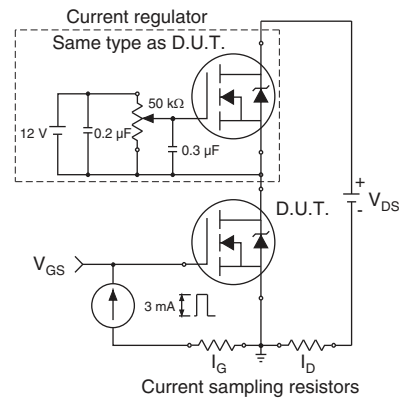
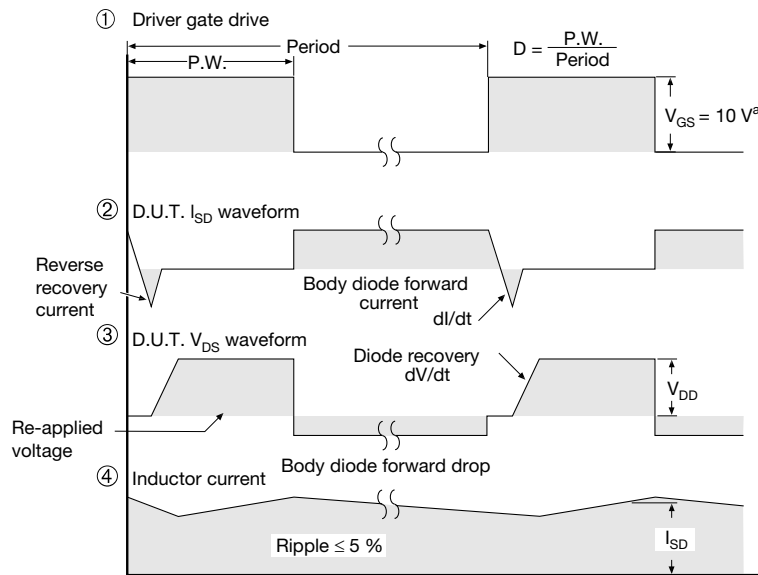
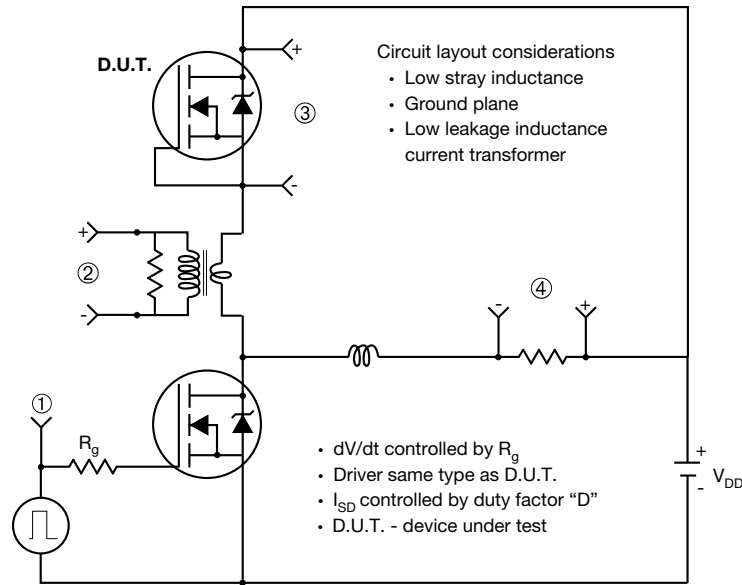


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



Note
a. $V_{GS} = 5 V$ for logic level devices

Fig. 14 - For N-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?90363.



TO-220-1



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.24	4.65	0.167	0.183
b	0.69	1.02	0.027	0.040
b(1)	1.14	1.78	0.045	0.070
c	0.36	0.61	0.014	0.024
D	14.33	15.85	0.564	0.624
E	9.96	10.52	0.392	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.10	6.71	0.240	0.264
J(1)	2.41	2.92	0.095	0.115
L	13.36	14.40	0.526	0.567
L(1)	3.33	4.04	0.131	0.159
Ø P	3.53	3.94	0.139	0.155
Q	2.54	3.00	0.100	0.118

ECN: E21-0621-Rev. D, 04-Nov-2021
 DWG: 6031

Note

- M* = 0.052 inches to 0.064 inches (dimension including protrusion), heatsink hole for HVM



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